

HSC226

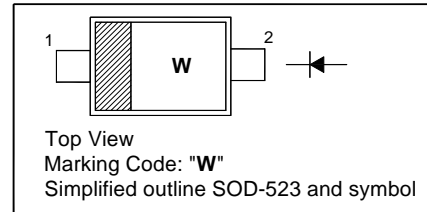
Silicon Schottky Barrier Diode

Features

- Low reverse current
- Ultra small flat package is suitable for surface mount design

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

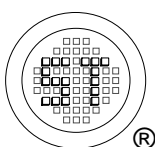


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	25	V
Forward Current	I_F	50	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	200	mA
Junction Temperature Range	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 5\text{ mA}$	V_F	0.33 0.38	V
Reverse Current at $V_R = 20\text{ V}$	I_R	0.45	μA
Junction Capacitance at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_J	20	pF



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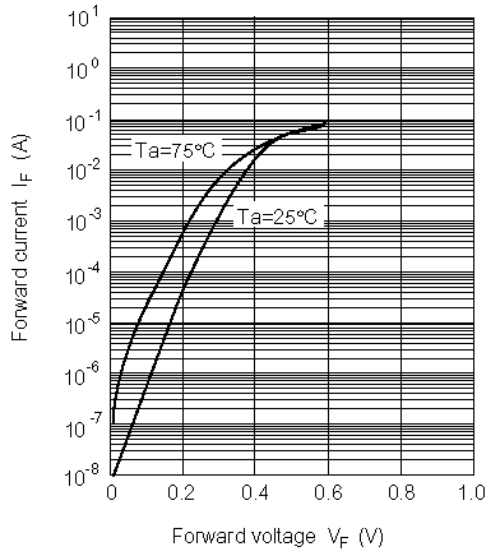


Fig.1 Forward current Vs. Forward voltage

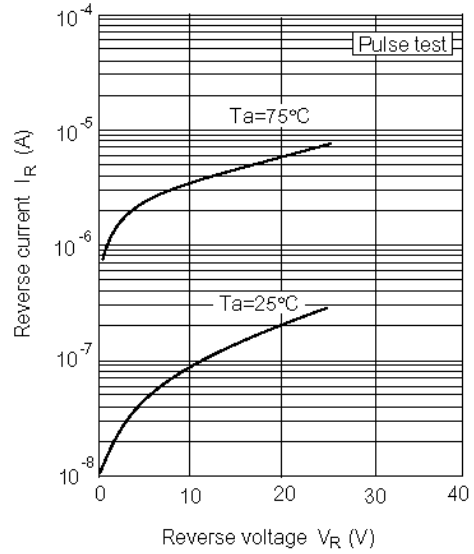
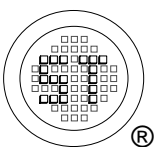


Fig.2 Reverse current Vs. Reverse voltage

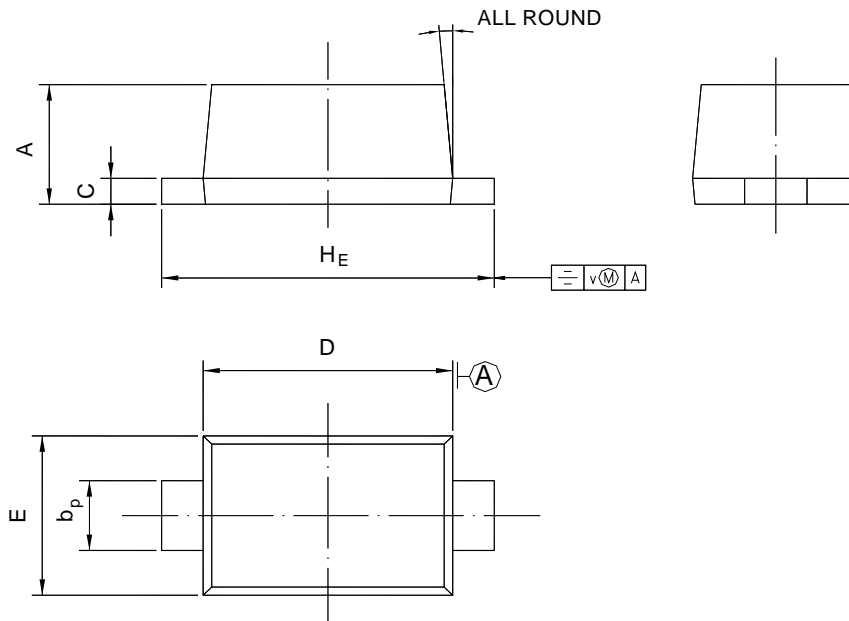


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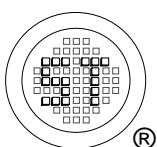
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b _p	C	D	E	H _E	V	
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°



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